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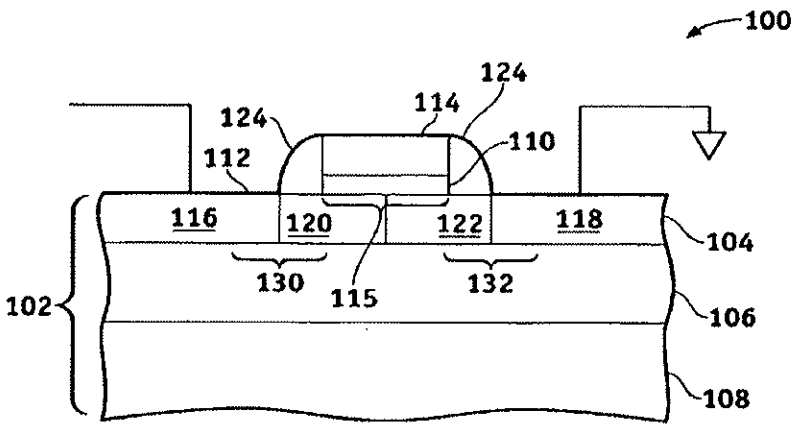
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(54) **Title:** ELECTROSTATIC DISCHARGE PROTECTION DEVICES AND METHODS FOR PROTECTING SEMICONDUCTOR DEVICES AGAINST ELECTROSTATIC DISCHARGE EVENTS



(57) **Abstract:** Methods and devices are provided for protecting semiconductor devices against electrostatic discharge events. An electrostatic discharge protection device (100) comprises a silicon substrate (104), a P+- type anode region (116) disposed within the silicon substrate, and an N-well device region (120) disposed within the silicon substrate in series with the P+-type anode region. A first P-well device region (122) is disposed within the silicon substrate in series with the first N-well device region and an N+-type cathode region (1 18) is disposed within the silicon substrate. A gate electrode (1 14) is disposed at least substantially overlying the first N-well and P-well device regions of the silicon substrate.

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